NL17SV16XV5T2

Ultra-Low Voltage Buffer

The NL17SV16XV5T2 is an ultra−high performance single Buffer fabricated in sub−micron silicon gate (0.35 μ) CMOS technology with excellent performance down to 0.9 V. This device is ideal for extremely high−speed and high−drive applications. Additionally, limitations of board space are no longer a constraint. The very small SOT−553 makes this device fit most tight designs and spaces.

The internal circuit is composed of three stages; including a buffered output which provides high noise immunity and stable output. The NL17SV16XV5T2 input structure provides protection when voltages up to 3.6 V are applied.

Features

- Extremely High Speed: 1.5 ns (Typ) at V_{CC} = 3.3 V
- Designed for 0.9 V to 3.6 V Operation
- Over Voltage Tolerance* (OVT) Input
  Permits Logic Translation
- Balanced ±24 mA Output Drive @ 3.3 Volts
- Near Zero Static Supply Current
- Ultra−Tiny SOT−553 5 Pin Package only 1.6 x 1.6 mm Footprint

Applications

- Cellular
- Digital Camera
- PDA
- Digital Video

*Over Voltage Tolerance (OVT) enables pins to function outside (higher) of their operating voltages, with no damage to the devices or to signal integrity.

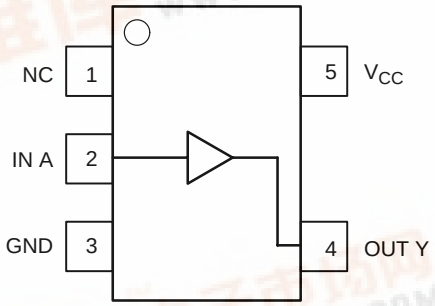

Figure 1. Pinout (Top View)

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SOT−553
CASE 463B

MARKING DIAGRAM

UN = Specific Device Code
D = Date Code

PIN ASSIGNMENT	
1	NC
2	IN A
3	GND
4	OUT Y
5	V_{CC}

FUNCTION TABLE

Input A	Output Y
L	L
H	H

ORDERING INFORMATION

Device	Package	Shipping†
NL17SV16XV5T2	SOT−553	4000 Tape & Reel (178 mm)

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Rating		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to + 4.6	V
V_I	DC Input Voltage		−0.5 to + 4.6	V
V_O	DC Output Voltage		−0.5 to V_{CC} +0.5	V
I_{IK}	DC Input Diode Current	V_I < GND	±50	mA
I_{OK}	DC Output Diode Current	V_O = GND V_O = V_{CC}	−50 +50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±50	mA
I_{GND}	DC Ground Current per Ground Pin		±50	mA
T_{STG}	Storage Temperature Range		− 65 to +150	°C
T_L	Lead Temperature, 1.0 mm from Case for 10 seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)		250	°C/W
P_D	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen index: 28 to 34	UL 94 V−0 @ 0125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	2000 300	V

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum−rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2 ounce copper trace no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	Digital Input Voltage		0	3.6	V
V_{out}	Output Voltage		0	V_{CC}	V
I_{OH}/I_{OL}	Output Current	V_{CC} = 3.0 V to 3.6 V V_{CC} = 2.3 V to 2.7 V V_{CC} = 1.65 V to 1.95 V V_{CC} = 1.4 V to 1.6 V V_{CC} = 1.1 V to 1.3 V V_{CC} = 0.9 V		±24 ±18 ±6 ±4 ±2 ±0.1	mA
t_A	Operating Temperature Range. All Package Types		−40	+85	°C
t_r, t_f	Input Rise or Fall Time	V_{CC} = 3.3V ± 0.3 V	0	10	nS/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

DC CHARACTERISTICS– Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC}	T_A = 25°C		T_A = −40 to 85°C		Unit
				Min	Max	Min	Max	
V_{IH}	High Level Input Voltage		0.90 1.10 ≤= V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 1.6 2.0		0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 1.6 2.0		V
V_{IL}	Low Level Input Voltage		0.90 1.10 ≤ V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.7 0.8		0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.7 0.8	V
V_{OH}	High Level Output Voltage	I_{OH} = −100 μA	0.90 1.10 ≤ V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	V_{CC} − 0.1 V_{CC} − 0.1 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2		V_{CC} − 0.1 V_{CC} − 0.1 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2		V
		I_{OH} = −2.0 mA	1.10 ≤ V_{CC} ≤ 1.30	0.75 x V_{CC}		0.75 x V_{CC}		
		I_{OH} = −4.0 mA	1.40 ≤ V_{CC} ≤ 1.60	0.75 x V_{CC}		0.75 x V_{CC}		
		I_{OH} = −6.0 mA	1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70	1.25 2.0		1.25 2.0		
		I_{OH} = −12 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	1.8 2.2		1.8 2.2		
		I_{OH} = −18 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	1.7 2.4		1.7 2.4		
		I_{OH} = −24 mA	2.70 ≤ V_{CC} ≤ 3.60	2.2		2.2		
V_{OL}	Low Level Output Voltage Low Level Output Voltage	I_{OL} = 100 μA	0.90 1.10 ≤ V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.1 0.1 0.2 0.2 0.2 0.2		0.1 0.1 0.2 0.2 0.2 0.2	V
		I_{OL} = 2.0 mA	1.10 ≤ V_{CC} ≤ 1.30		0.25 x V_{CC}		0.25 x V_{CC}	
		I_{OL} = 4.0 mA	1.40 ≤ V_{CC} ≤ 1.60		0.25 x V_{CC}		0.25 x V_{CC}	
		I_{OL} = 6.0 mA	1.65 ≤ V_{CC} ≤ 1.95		0.3		0.3	
		I_{OL} = 12 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.4 0.4		0.4 0.4	
		I_{OL} = 18 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.6 0.4		0.6 0.4	
		I_{OL} = 24 mA	2.70 ≤ V_{CC} ≤ 3.60		0.55		0.55	
I_{IN}	Input Leakage Current	0 = V_I = 3.6 V	0.90 to 3.60		±0.1		±0.9	μA
I_{OFF}	Power Off Leakage Current		0		1		5	μA
I_{CC}	Quiescent Supply Current	V_I = V_{CC} or GND V_{CC} = V_I = 3.6 V	0.90 to 3.60		0.9		5 ±5	μA

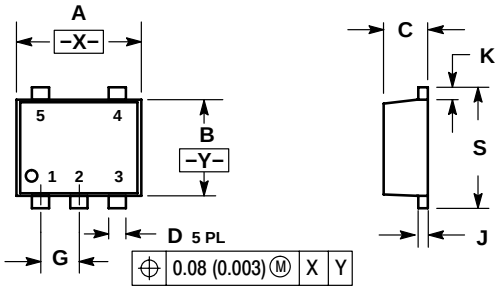
AC CHARACTERISTICS (Input $t_r = t_f = 3.0$ nS)

Symbol	Parameter	−40°C		25°C			85°C		Unit
		Condition	V_{CC}	Min	Typ	Max	Min	Max	
T_{PHL}, T_{PLH}	Propagation Delay	C_L = 15 pF, R_L = 1.0 MΩ	0.90		20				nS
		C_L = 15 pF, R_L = 2.0 kΩ	1.10 ≤ V_{CC} ≤ 1.30	2.0	6.0	13	1.0	16.9	nS
			1.40 ≤ V_{CC} ≤ 1.60	1.0	3.2	6.1	1.0	7.0	
		C_L = 30 pF, R_L = 500 kΩ	1.65 ≤ V_{CC} ≤ 1.95	1.0	2.0	5.2	1.0	6.2	nS
			2.30 ≤ V_{CC} ≤ 2.70	0.8	1.2	3.7	0.7	4.4	
			2.70 ≤ V_{CC} ≤ 3.60	0.7	1.0	3.3	0.6	3.8	
C_{IN}	Input Capacitance		0		2.0				pF
C_{OUT}	Output Capacitance		0		4.5				pF
C_{PD}	Power Dissipation Capacitance	V_I = 0 V or V_{CC} F = 10 MHz	0.90 to 3.60		20				pF

NL17SV16XV5T2

PACKAGE DIMENSIONS

SOT−553
5−LEAD PACKAGE
CASE 463B−01
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.50	1.70	0.059	0.067
B	1.10	1.30	0.043	0.051
C	0.50	0.60	0.020	0.024
D	0.17	0.27	0.007	0.011
G	0.50 BSC		0.020 BSC	
J	0.08	0.18	0.003	0.007
K	0.10	0.30	0.004	0.012
S	1.50	1.70	0.059	0.067

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PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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